

N-Channel Reduced Q_g , Fast Switching MOSFET

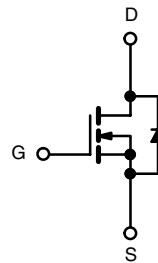
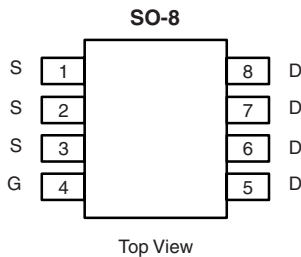
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.0185 at $V_{GS} = 10$ V	9
	0.030 at $V_{GS} = 4.5$ V	7

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- High-Efficient PWM Optimized
- 100 % UIS and R_g Tested



RoHS
COMPLIANT
HALOGEN
FREE
Available



N-Channel MOSFET

Ordering Information: Si4800BDY-T1-E3 (Lead (Pb)-free)
Si4800BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	30		V	
Gate-Source Voltage	V_{GS}	± 25			
Continuous Drain Current ($T_J = 150$ °C) ^{a, b}	I_D	$T_A = 25$ °C	9	6.5	A
		$T_A = 70$ °C	7.0	5.0	
Pulsed Drain Current (10 μ s Pulse Width)	I_{DM}	40			
Continuous Source Current (Diode Conduction) ^{a, b}	I_S	2.3			
Avalanche Current	I_{AS}	15		mJ	
Single-Pulse Avalanche Energy	E_{AS}	11.25			
Maximum Power Dissipation ^{a, b}	P_D	$T_A = 25$ °C	2.5	1.3	W
		$T_A = 70$ °C	1.6	0.8	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limits		Unit	
		Typ.	Max.		
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	40	50	°C/W
		Steady State	70	95	
Maximum Junction-to-Foot (Drain)	R_{thJF}	Steady State	24	30	

Notes:

a. Surface Mounted on FR4 board.

b. $t \leq 10$ s.

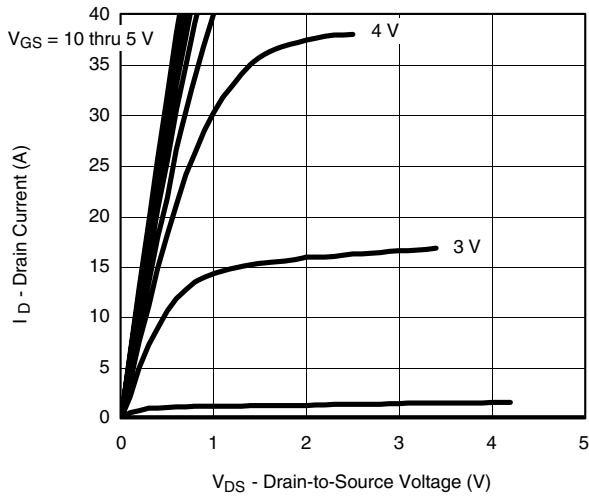
MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	0.8		1.8	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 10\ \text{V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 9\ \text{A}$		0.0155	0.0185	Ω
		$V_{GS} = 4.5\ \text{V}$, $I_D = 7\ \text{A}$		0.023	0.030	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}$, $I_D = 9\ \text{A}$		16		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.3\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.75	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\ \text{V}$, $V_{GS} = 5.0\ \text{V}$, $I_D = 9\ \text{A}$		8.7	13	nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			3.5		
Gate Resistance	R_g		0.5	1.4	2.2	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}$, $R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 10\ \text{V}$, $R_g = 6\ \Omega$		7	15	ns
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			32	50	
Fall Time	t_f			14	25	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.3\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		30	60	

Notes:

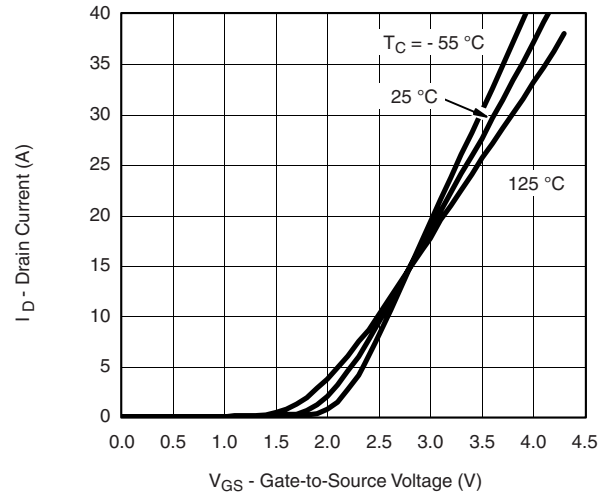
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

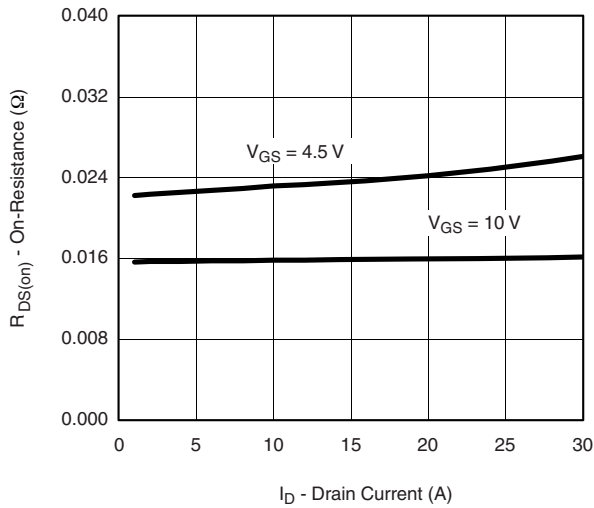
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



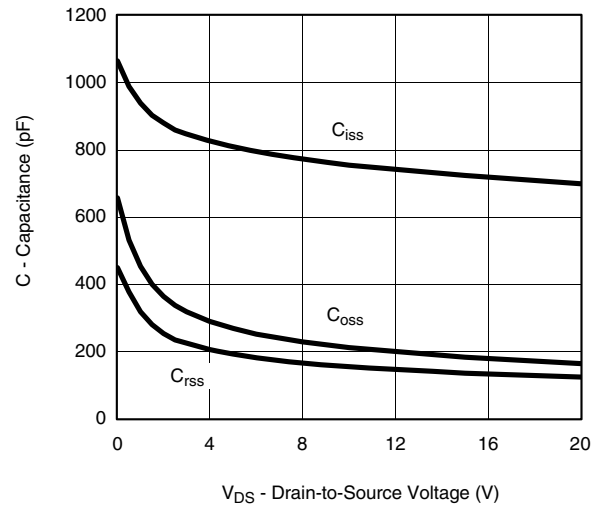
Output Characteristics



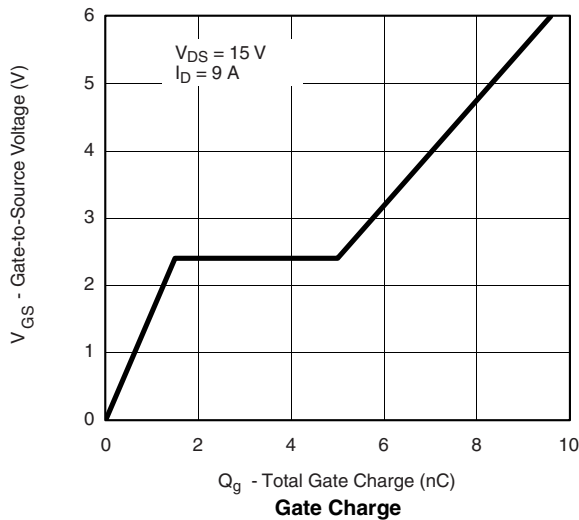
Transfer Characteristics



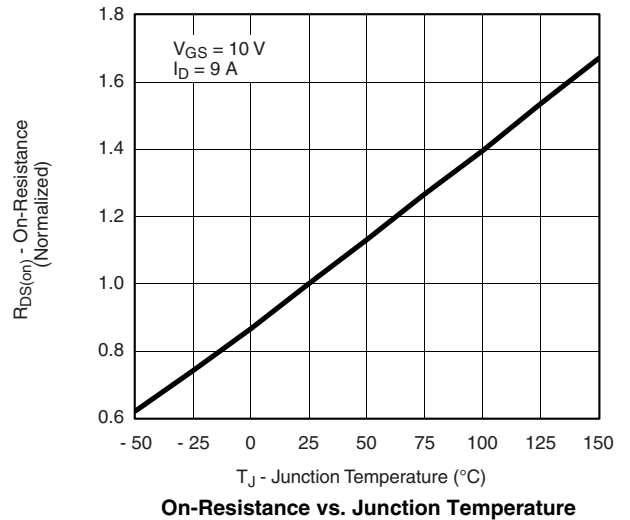
On-Resistance vs. Drain Current



Capacitance

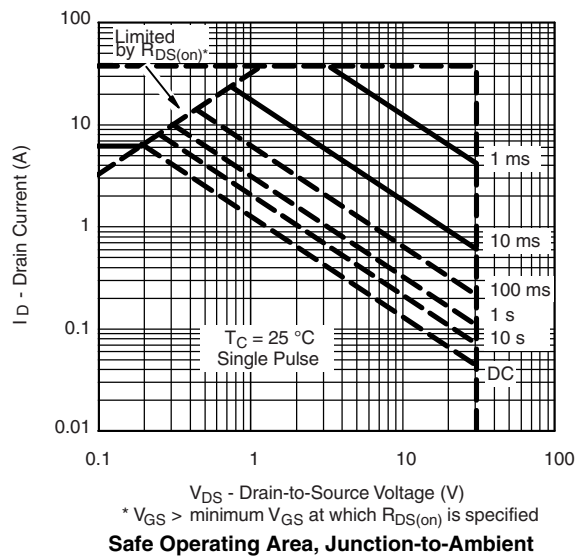
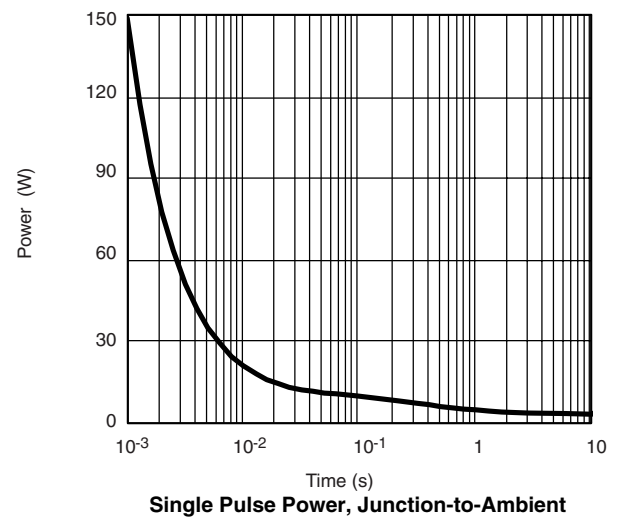
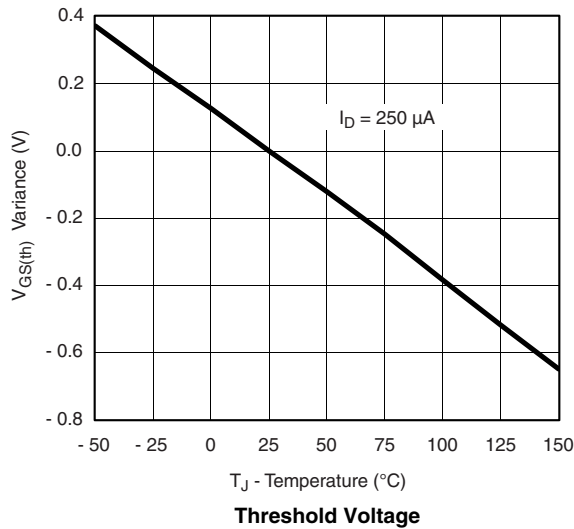
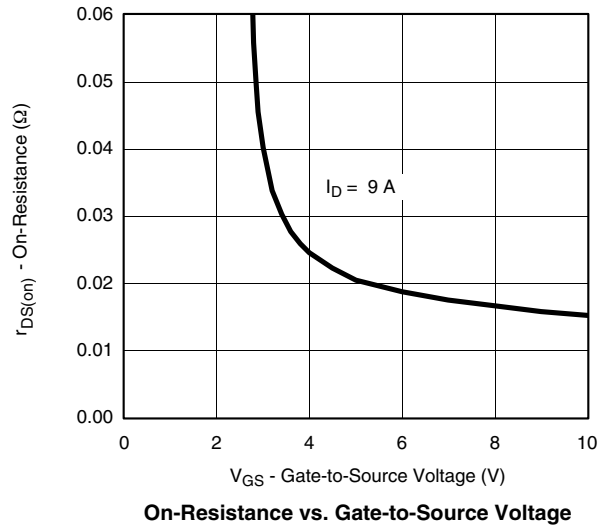
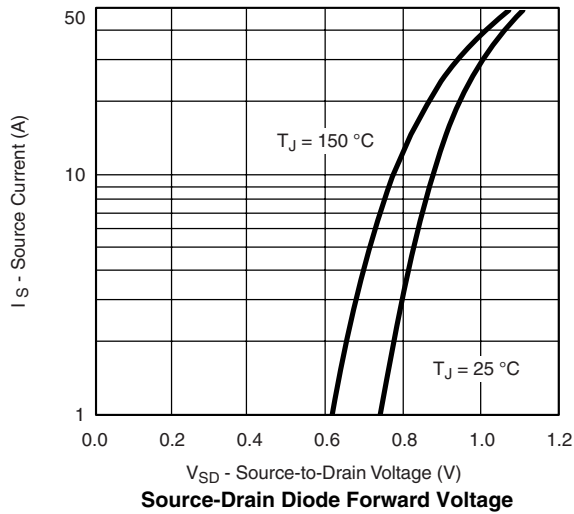


Gate Charge

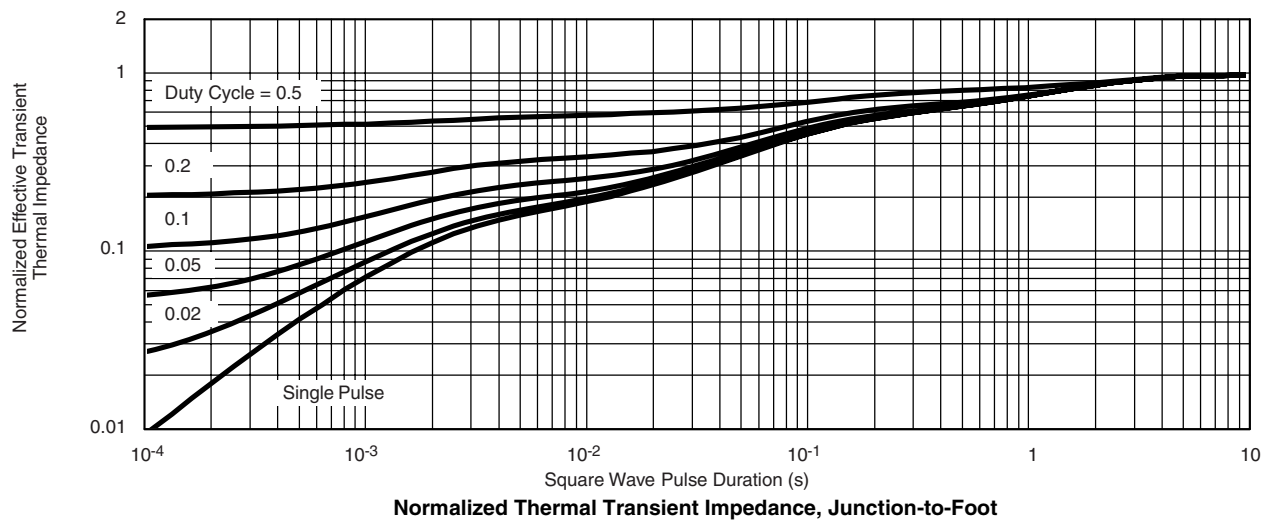
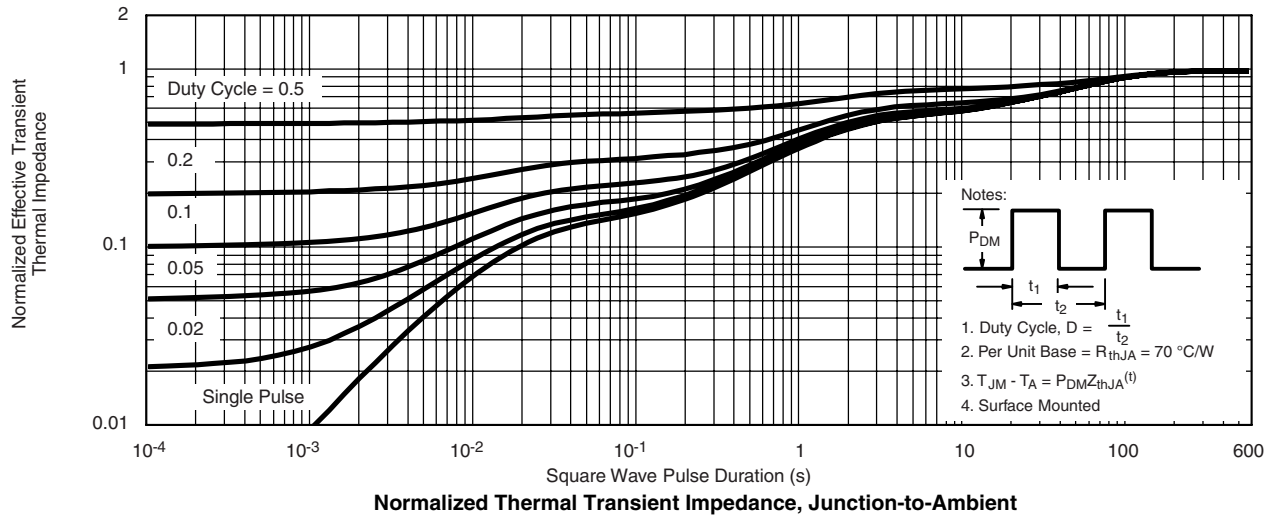


On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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